2SK3022

Silicon N-channel power MOSFET

■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON resistance R_{on}
- No secondary breakdown
- Low-voltage drive
- High electrostatic energy capability

■ Applications

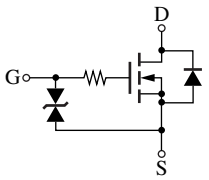
- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Package

- Code
  U-G2
- Pin Name
  1: Gate
  2: Drain
  3: Source

■ Marking Symbol: K3022

■ Internal Connection



■ Absolute Maximum Ratings $T_C = 25°C$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	60	V
Gate-source surrender voltage	V_{GSS}	±20	V
Drain current	I_D	±5	A
Peak drain current	I_{DP}	±15	A
Avalanche energy capability *	EAS	6.25	mJ
Power dissipation	P_D	10	W
$T_a = 25°C$		1	
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Note) *: L = 0.5 mH, I_L = 5 A, 1 pulse

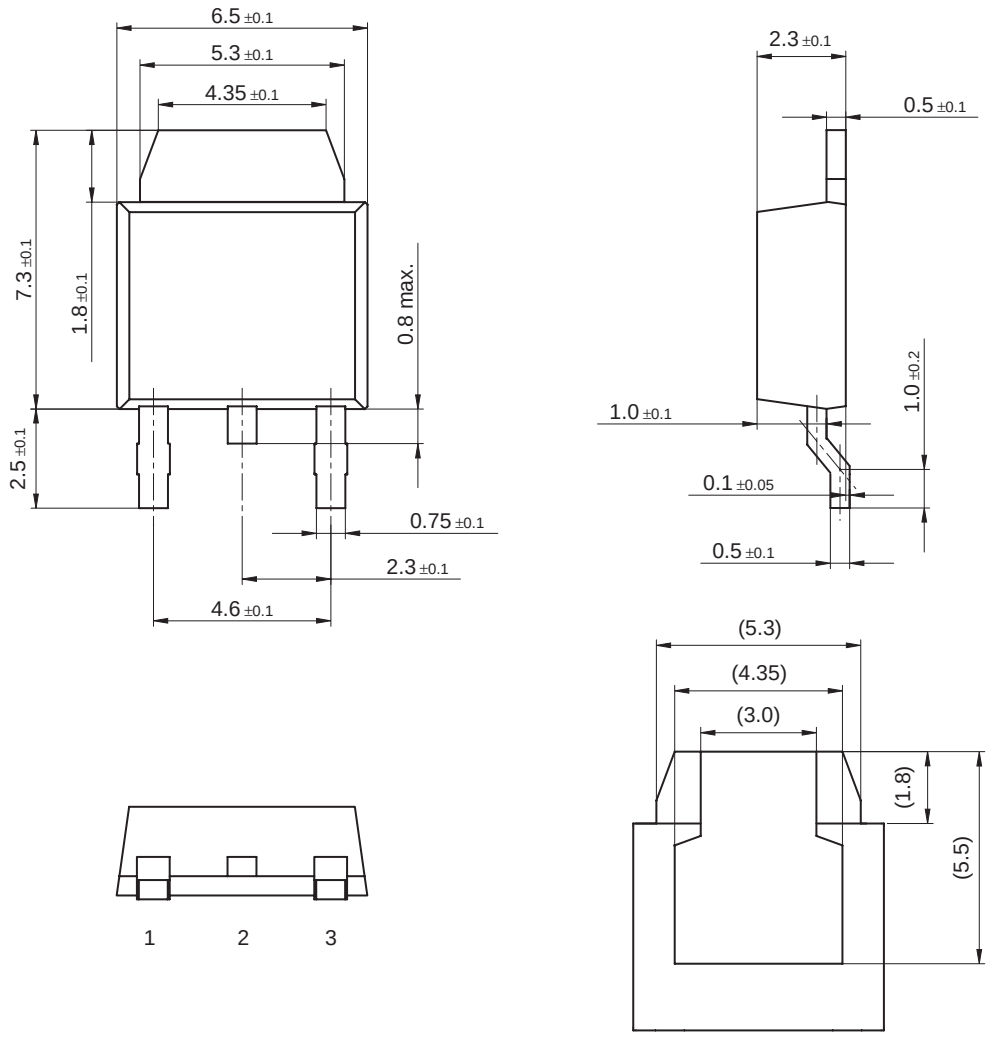
■ Electrical Characteristics $T_C = 25°C \pm 3°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	I_D = 1 mA, V_{GS} = 0	60			V
Drain-source cutoff current	I_{DSS}	V_{DS} = 50 V, V_{GS} = 0			10	μA
Gate-source cutoff current	I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0			±10	μA
Gate threshold voltage	V_{th}	V_{DS} = 10 V, I_D = 1 mA	1.0		2.5	V
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 3 A	2	4		S
Drain-source ON resistance	$R_{DS(on)1}$	V_{GS} = 10 V, I_D = 3 A		90	130	mΩ
	$R_{DS(on)2}$	V_{GS} = 4 V, I_D = 3 A		130	200	
Diode forward voltage	V_{DSF}	I_{DR} = 5 A, V_{GS} = 0			−1.3	V
Short-circuit forward transfer capacitance (Common source)	C_{iss}	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz		220		pF
Short-circuit output capacitance (Common source)	C_{oss}			90		pF
Reverse transfer capacitance (Common source)	C_{rss}			50		pF
Turn-on delay time	$t_{d(on)}$	V_{DD} = 30 V, I_D = 3 A, R_L = 10 Ω		15		ns
Rise time	t_r	V_{GS} = 10 V		30		ns
Fall time	t_f			170		ns
Turn-off delay time	$t_{d(off)}$			550		ns
Thermal resistance (ch-c)	$R_{th(ch-c)}$				12.5	°C/W
Thermal resistance (ch-a)	$R_{th(ch-a)}$				125	°C/W

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

U-G2

Unit: mm


6.5 ±0.1
5.3 ±0.1
4.35 ±0.1
7.3 ±0.1
1.8 ±0.1
0.8 max.
2.5 ±0.1
0.75 ±0.1
2.3 ±0.1
4.6 ±0.1
1
2
3
2.3 ±0.1
0.5 ±0.1
1.0 ±0.2
1.0 ±0.1
0.1 ±0.05
0.5 ±0.1
(5.3)
(4.35)
(3.0)
(1.8)
(5.5)

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